

## TAPERED AMPLIFIERS Semiconductor Optical Amplifier

### Distributor

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TOPTICA

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### General Product Information

Product	Application
780 nm Tapered Amplifier	Spectroscopy
14 Pin Butterfly Package (non hermetic)	
with PM Fiber and FC/APC Connector (Input)	
and collimated Output Beam	
and commated Output Beam	



### Absolute Maximum Ratings

Symbol	Unit	min	typ	max
Ts	°C	-40		85
T <sub>C</sub>	°C	15		35
T <sub>chip</sub>	°C	15		35
I <sub>F</sub>	А			5
V <sub>R</sub>	V			2
P <sub>opt</sub>	W			3.2
	T <sub>s</sub> T <sub>c</sub> T <sub>chip</sub> I <sub>F</sub> V <sub>R</sub>	$T_{s} \circ C$ $T_{chip} \circ C$ $I_{F} A$ $V_{R} V$	$\begin{array}{c c} T_{s} & ^{\circ}C & -40 \\ T_{c} & ^{\circ}C & 15 \\ \hline T_{chip} & ^{\circ}C & 15 \\ I_{F} & A \\ V_{R} & V \end{array}$	T_s°C-40T_c°C15 $T_{chip}$ °C15 $I_F$ A $V_R$ V

### **Recommended Operational Conditions**

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T <sub>C</sub>	°C	15		50
Operational Temperature at Chip	T <sub>chip</sub>	°C	15	25	35
Forward Current	Ι <sub>F</sub>	А			4.5
Input Power	P <sub>input</sub>	mW	10		80
Output Power	P <sub>opt</sub>	W			3

### Characteristics at T<sub>chip</sub>

Parameter	Symbol	Unit	min	typ	max
Wavelength	$\lambda_{c}$	nm		780	
Gain Width (FWHM)	Δλ	nm		20	
Temp. Coefficient of Wavelength	dλ / dT	nm / K		0.3	
Operational Current	I <sub>op Gain</sub>	А			4.5
Output Power	P <sub>opt</sub>	W	3.0		
Amplification	G	dB		23	

### Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Measurement Conditions / Comments				
non condensing				
with proper injection from a seed laser				

Measurement Conditions / Comments			
$P_{opt} =$ with proper injection from a seed laser			
at recommended maximum forward current			

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				cont'd
Symbol	Unit	min	typ	max
d <sub>out  </sub>	mm		1	
d <sub>out⊥</sub>	mm		1	
$\Theta_{out}$	mrad		3	
$\Theta_{\text{out}\perp}$	mrad		3	
			TM	
	d <sub>out</sub>    d <sub>out⊥</sub> ⊖ <sub>out</sub>	d <sub>out</sub>    mm d <sub>out⊥</sub> mm ⊖ <sub>out</sub>    mrad	d <sub>out  </sub> mm d <sub>out⊥</sub> mm ⊖ <sub>out  </sub> mrad	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

Measurement Conditions / Comments				
Weasurement Conditions / Comments				
E field perpendicular to base plate				

### Thermoelectric Cooler

Parameter	Symbol	Unit	min	typ	max
Current	I <sub>TEC</sub>	А			2.5
Voltage	U <sub>TEC</sub>	V			5
Power Dissipation (total loss at case)	Ploss	W		10	
Temperature Difference	ΔΤ	К			20

## Thermistor (Standard NTC Type)

D 10		
R kΩ	10	
β	3892	
A	1.1293 x	10 <sup>-3</sup>
В	2.3410 x	10 -4
C	8.7755 x	10 <sup>-8</sup>
	•	

# $\label{eq:compared} \begin{array}{l} \mbox{Measurement Conditions / Comments} \\ \hline $T_{Chip} = 25^{\circ} \ C$ \\ \hline $R_1 / R_2 = e^{\beta (1/T_1 \cdot 1/T_2)} $ at $T_{LD} = $ 0^{\circ} \ \dots \ 50^{\circ} \ C$ \\ \hline $1/T = A + B(ln \ R) + C(ln \ R)^3$ } \end{array}$

Measurement Conditions / Comments

 $\begin{array}{ll} \mathsf{P}_{opt} = & 3 \ \mathsf{W} \\ \mathsf{P}_{opt} = & 3 \ \mathsf{W} \\ \mathsf{P}_{opt} = & 3 \ \mathsf{W} \\ \mathsf{P}_{opt} = & 3 \ \mathsf{W} \end{array}$ 

T: temperature in Kelvin R: resistance at T in Ohm

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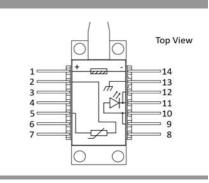
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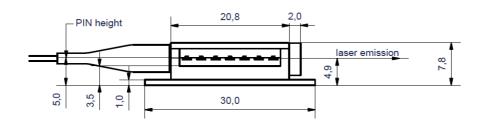
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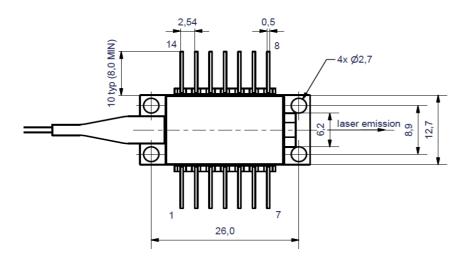
### Pin Assignment

1	Thermoelectric Cooler (+)	14	Thermoelectric Cooler (-)
2	Thermistor	13	Case
3	not connected	12	Amplifier (Cathode)
4	not connected	11	Amplifier (Cathode)
5	Thermistor	10	Amplifier (Anode)
6	not connected	9	Amplifier (Anode)
7	not connected	8	not connected



### Package Drawings





Caution. Excessive mechanical stress on the package can lead to a damage of the device. See <u>instruction manual</u> on www.toptica-eagleyard.com

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### Unpacking, Installation and Laser Safety

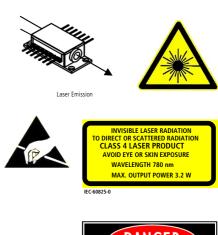
Unpacking the taperd amplifier should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The TPA diode type is known to be sensitive against thermal stress. It should not be operated without appropriate injection from a seed laser. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode. The chip should be protected against moisture. A water vapor content below 5000 ppm is recommended for applications with high reliability requirements.

This amplifier is designed for the setup of MOPA systems. Appropriate seed lasers are DFB lasers of the type EYP-DFB-xxxx-xxxx-1500-BFY12-000x with matching wavelengths. An external fiber isolator should be used between seed laser and amplifier in order to suppress backreflections that may disturb the emission spectrum of the seed laser and may cause mode-hops in case of wavelength tuning.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each tapered amplifier will come with an individual test protocol verifying the parameters given in this document.







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